

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS/008	SERIAL NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary) (37 CFR 1.98(b))				APPLICANT Pradip K. Roy et al.	
				FILING DATE March 10, 2004	GROUP Unknown

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER			ISSUE DATE	PATENTEE		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A									
	A.B									
	A.C									
	A.D									
	A.E									
	A.F									
	A.G									
	A.H									
	A.I									
	A.J									
	A.K									

## FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
<i>SKR</i>	A.L	EP0684650 B1	08/29/2001	EP	H01L	29/786	
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

## OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

<i>SKR</i>	A.R	Stephen St. Onge and Mark Dupuis, <u>Innovations in Silicon Germanium Bicmos Processing</u> , Semiconductor Fabtech - 12th Edition, pp 195-199, published July, 2000.
	A.S	
	A.T	

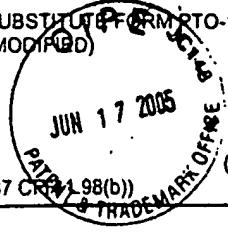
EXAMINER

*Stephen St. Onge*

DATE CONSIDERED

*10/13/05*

EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered.  
Include a copy of this form with next communication to Applicant.

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE							ATTY. DOCKET NO. TPS-008	SERIAL NO. 10/797,425
 (37 CFR 1.98(b))		INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)							APPLICANT Pradip K. Roy et al.	
									FILING DATE March 10, 2004	GROUP 2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A.A	6	4	2	3	6	3	2	07/23/2002	Samavedam et al.		438	652	07/21/2000
	A.B													
	A.C													
	A.D													
	A.E													
	A.F													
	A.G													
	A.H													
	A.I													
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	A.L						
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

## OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

<i>SP</i>	A.R	Luo et al., <u>Seedless Method of Forming a Silicon Germanium Layer on a Gate Dielectric Layer</u> , US 2004/0009680 A1; publication date 01/15/2004; filed 07/10/2002; U.S. Class 438/933
<i>SP</i>	A.S	Uejima et al., <u>Highly Reliable Poly-SiGe/Amorphous-Si Gate CMOS</u> , Electron Devices Meeting; IEDM Technical Digest; pp. 445-448; 12/10/2000
	A.T	

EXAMINER		DATE CONSIDERED
<i>SP</i> S. Lee		01/13/05

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